HGN099N15S P-1

150V N-Ch Power MOSFET

Feature

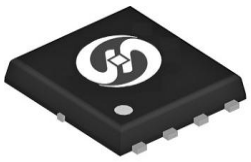
◇ High Speed Power Switching
◇ Enhanced Body diode dv/dt capability
◇ Enhanced Avalanche Ruggedness
◇ 100% UIS Tested, 100% Rg Tested
◇ Lead Free, Halogen Free

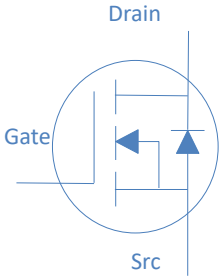
V_{DS}		150	V
$R_{DS(on),typ}$	V_{GS}=10V	9.5	mΩ
$I_{D\ (Sillicon\ Limited)}$		80	A
$I_{D\ (Package\ Limited)}$		60	A

Application

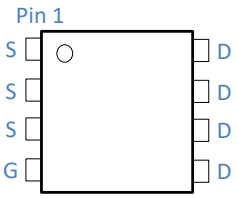
◇ Synchronous Rectification in SMPS
◇ Hard Switching and High Speed Circuit
◇ DC/DC in Telecoms and Industrial

DFN5x6





Part Number	Package	Marking
HGN099N15S	DFN5*6	GN099N15S



Absolute Maximum Ratings at T_j=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C=25℃	80	A
		T_C=100℃	50	
Continuous Drain Current (Package Limited)		T_C=25℃	60	
Drain to Source Voltage	V_{DS}	-	150	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	350	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C=25℃	320	mJ
Power Dissipation	P_D	T_C=25℃	139	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to150	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	55	℃/W
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.9	℃/W

Electrical Characteristics at T_j=25℃ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	150	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	2	3	4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=150V, T_j=25℃	-	-	1	μA
		V_{GS}=0V, V_{DS}=150V, T_j=100℃	-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	9.5	10.5	mΩ
Transconductance	g_{fs}	V_{DS}=5V, I_D=20A	-	50	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz	-	1.55	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=75V, f=1MHz	-	2212	-	pF
Output Capacitance	C_{oss}		-	330	-	
Reverse Transfer Capacitance	C_{rss}		-	9.5	-	
Total Gate Charge	Q_g(10V)	V_{DD}=75V, I_D=20A, V_{GS}=10V	-	26	-	nC
Gate to Source Charge	Q_{gs}		-	9	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	3	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=75V, I_D=20A, V_{GS}=10V, R_G=10Ω,	-	11	-	ns
Rise time	t_r		-	9	-	
Turn off Delay Time	$t_{d(off)}$		-	16	-	
Fall Time	t_f		-	8	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=75V, I_F=20A, dI_F/dt=100A/μs	-	80	-	ns
Reverse Recovery Charge	Q_{rr}		-	140	-	nC

Fig 1. Typical Output Characteristics

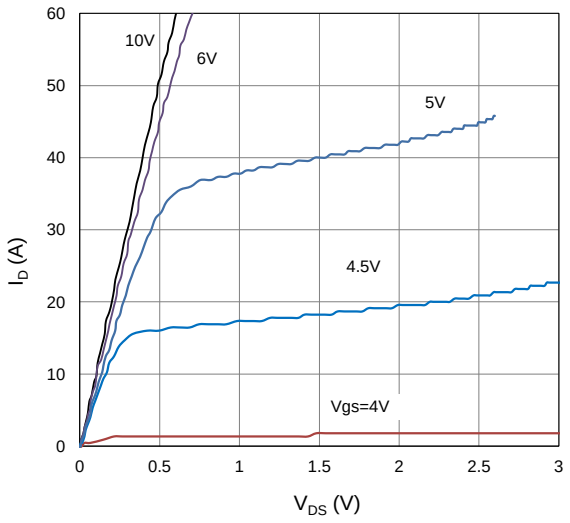


Figure 2. On-Resistance vs. Gate-Source Voltage

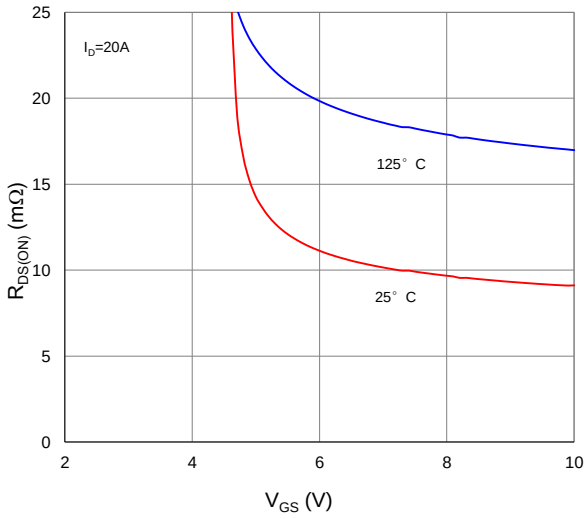


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

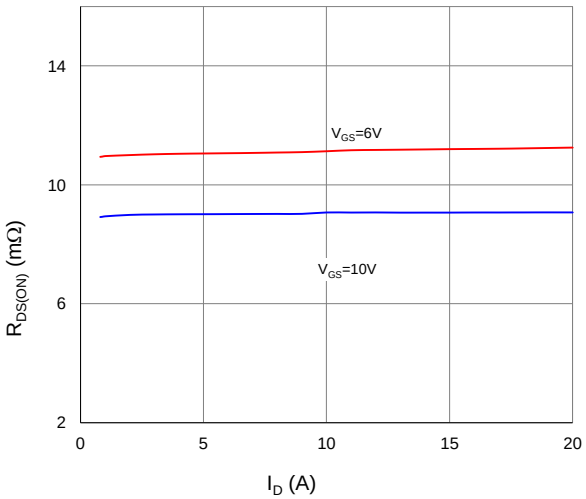


Figure 4. Normalized On-Resistance vs. Junction Temperature

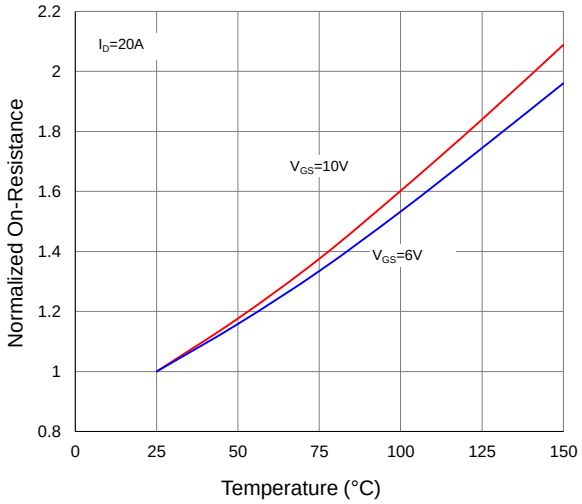


Figure 5. Typical Transfer Characteristics

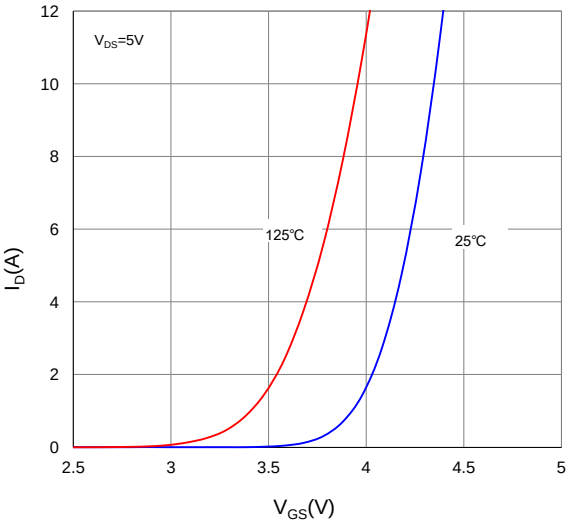


Figure 6. Typical Source-Drain Diode Forward Voltage

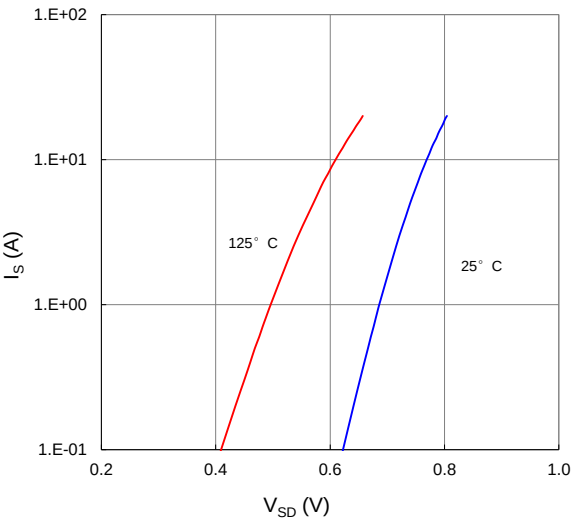


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

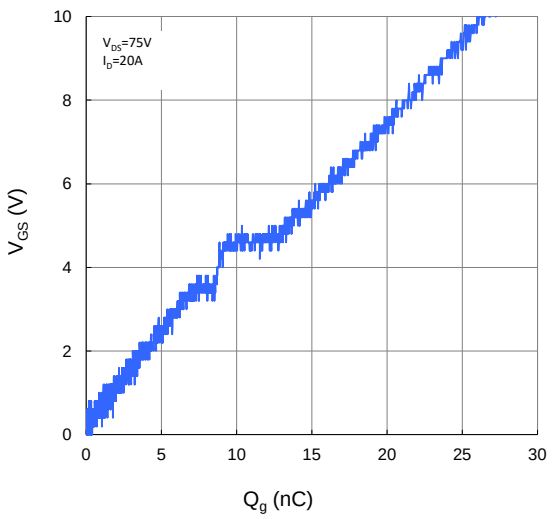


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

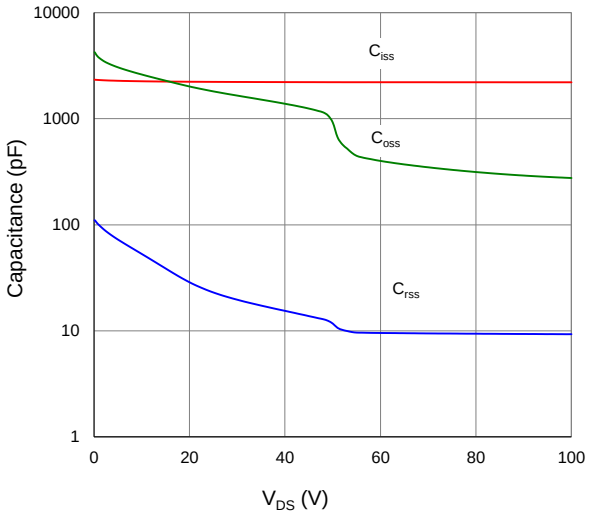


Figure 9. Maximum Safe Operating Area

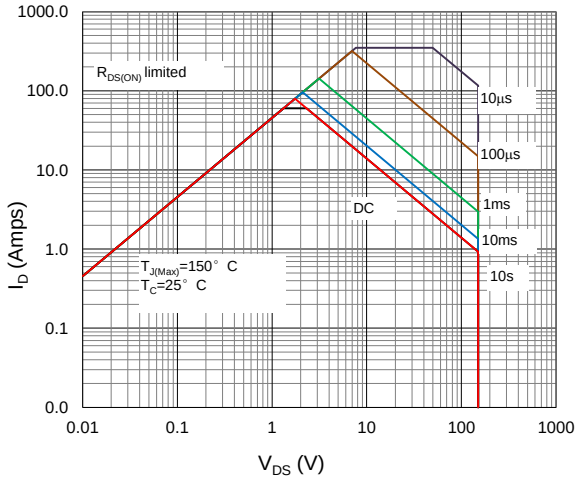


Figure 10. Maximun Drain Current vs. Case Temperature

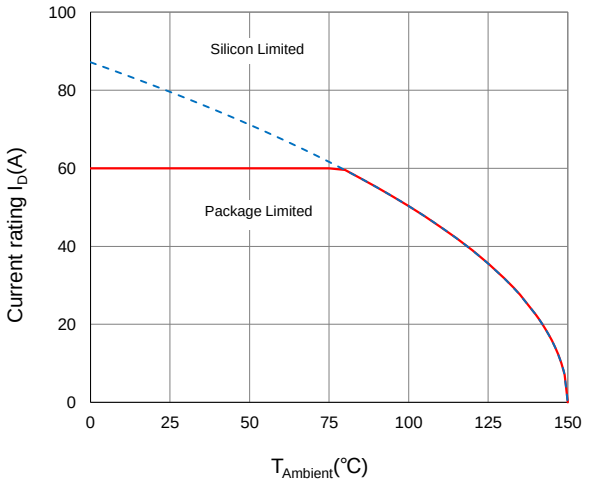
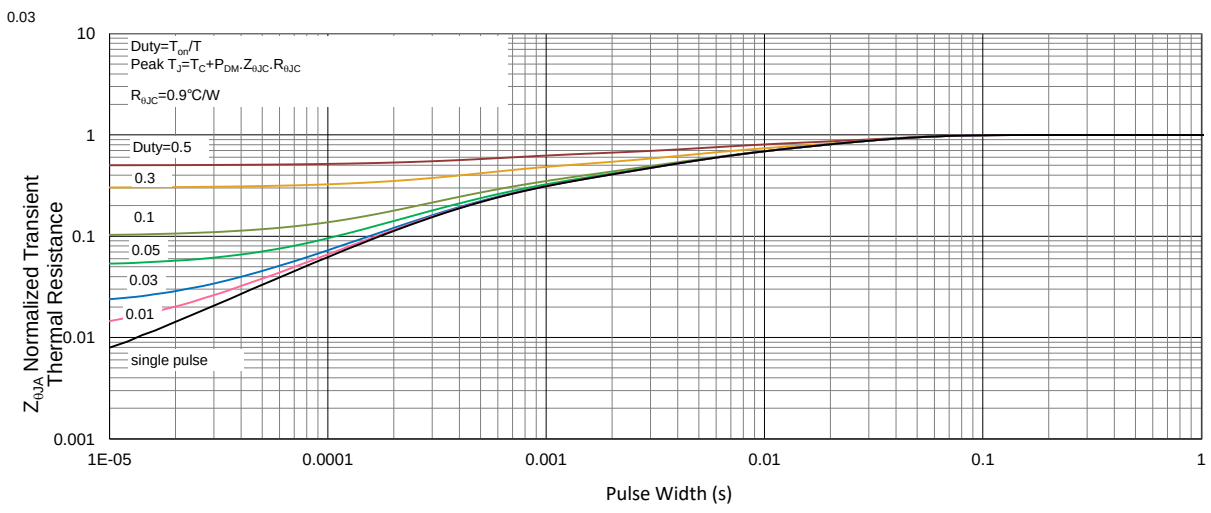
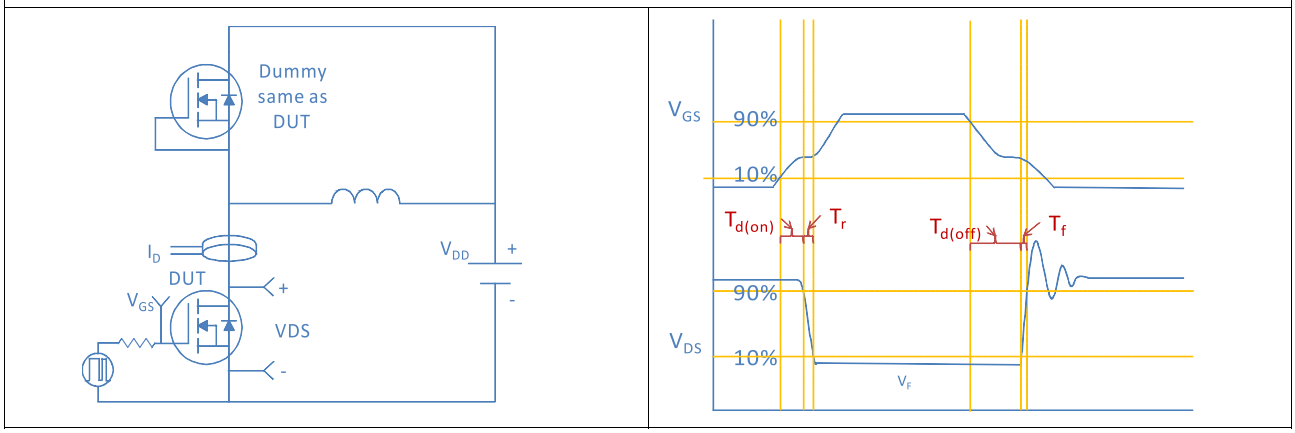


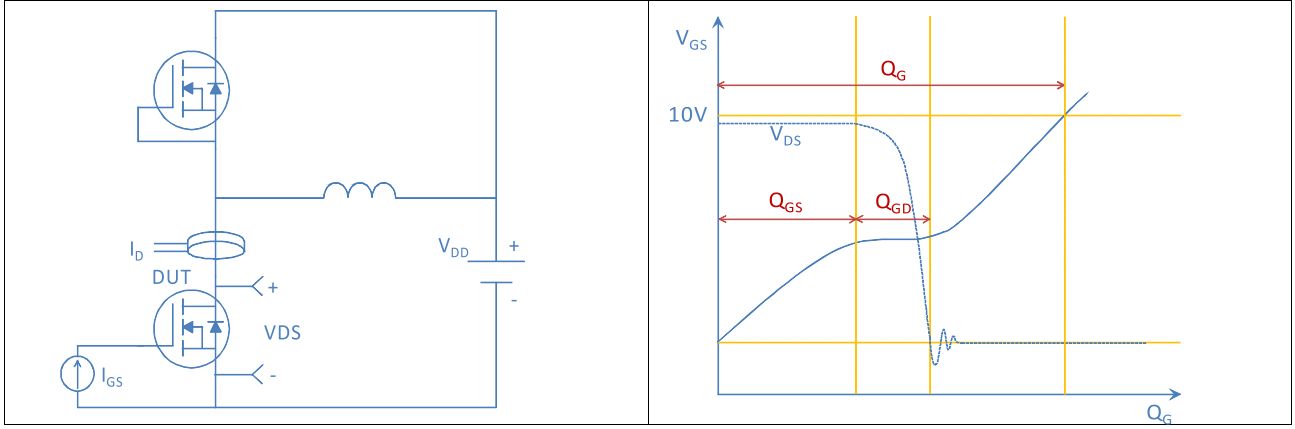
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



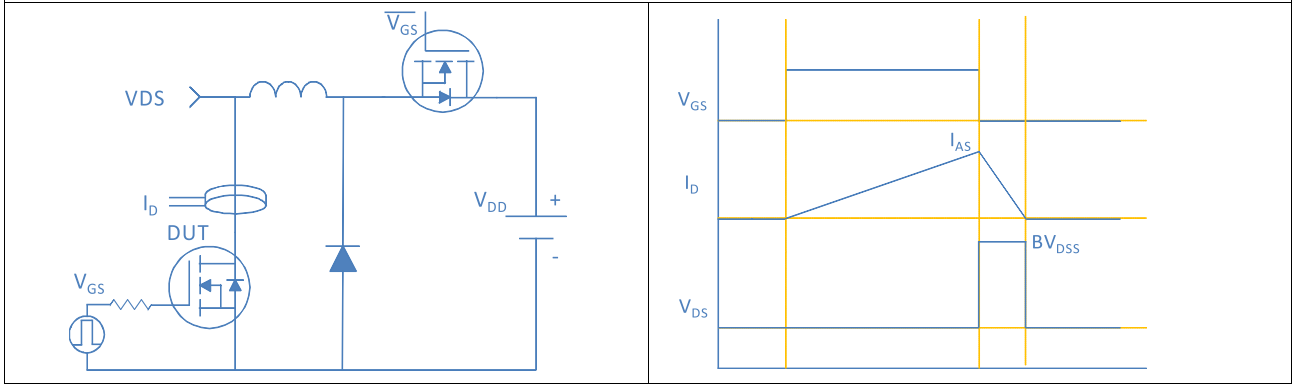
Inductive switching Test



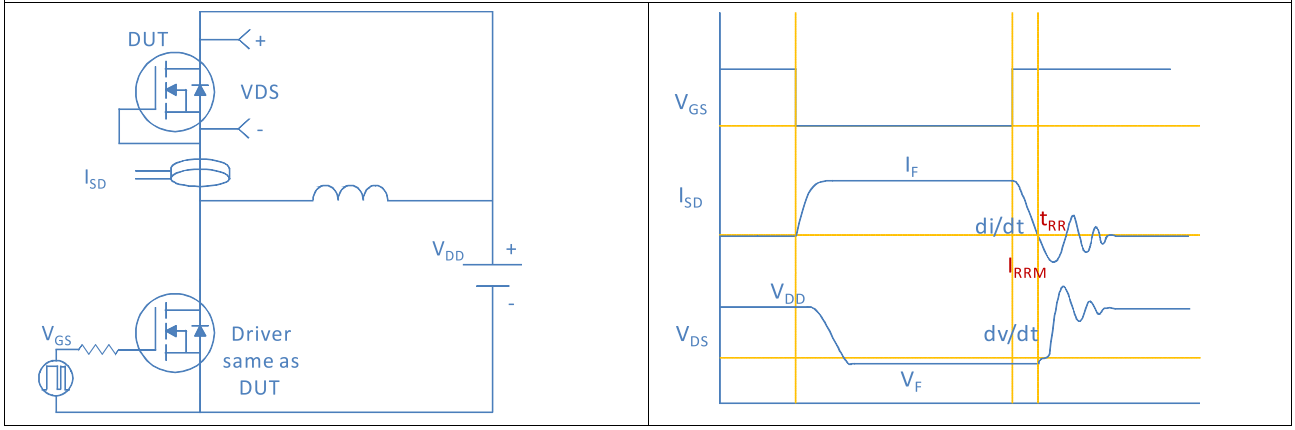
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

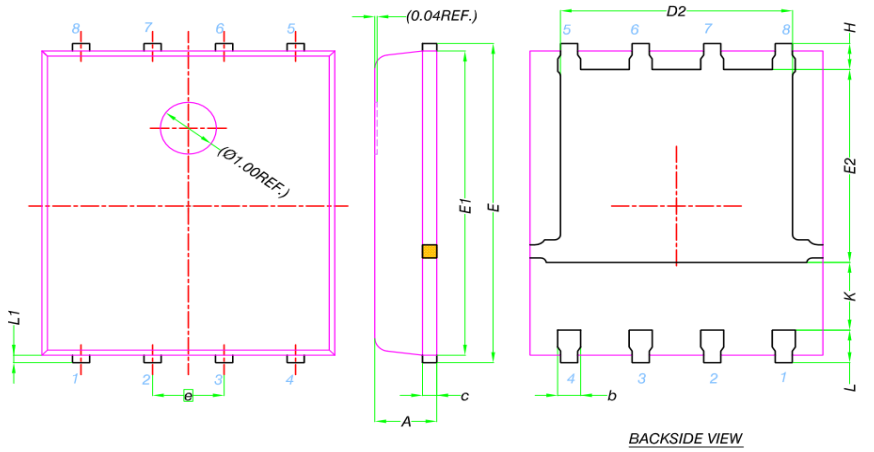


Diode Recovery Test

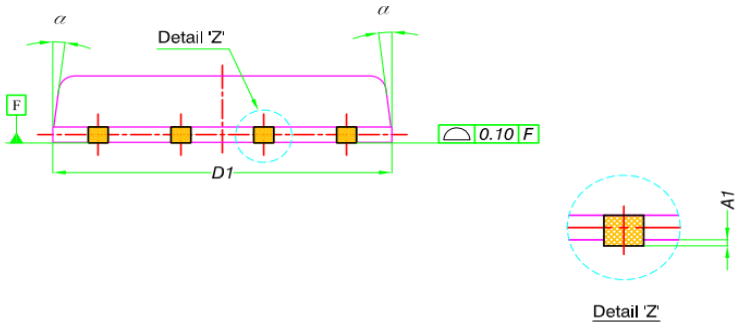


Package Outline

DFN5x6_P, 8 Leads



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0	---	0.05
b	0.33	0.40	0.50
c	0.20	0.25	0.30
D1	5.00	5.20	5.40
D2	3.80	4.10	4.25
E	6.00	6.15	6.30
E1	5.76	5.86	5.96
E2	3.52	3.72	3.92
e	1.27 BSC		
H	0.40	0.50	0.60
K	1.10	---	---
L	0.50	0.60	0.70
L1	0.08	0.15	0.22
α	0°	---	12°



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